

## SPECIFICATION OF LED CHIP CE1550-150 [ NIR ]

### 1) Commodity Type and Physical Characteristics.

1. Material	InGaAsP/InP(DH)	
2. Electrode	Top Side P (anode) side	: Au Alloy
	Bottom Side N (cathode) side	: Au Alloy
3. Electrode Pattern		Fig.1
4. Chip Size	510um*320um	Fig.1
5. Chip Thickness	260um	Fig.1
6. Emission Area	Φ150um	Fig.1

### 2) Electro-Optical Characteristics

Parameters	Symbol	Condition	min.	typ.	max.	unit
Forward Voltage	V <sub>f</sub>	I <sub>f</sub> =20mA		1.20	1.50	V
Reverse Current	I <sub>r</sub>	V <sub>r</sub> =5V			10	uA
Radiant Power	P <sub>o</sub>	I <sub>f</sub> =20mA		0.20		mW
Peak Wavelength	λ <sub>P</sub>	I <sub>f</sub> =20mA		1550		nm
Spectral Radiation Bandwidth	Δλ	I <sub>f</sub> =20mA		100		nm
RiseTime	t <sub>r</sub>	I <sub>f</sub> =20mA		10		ns
FallTime	t <sub>f</sub>	I <sub>f</sub> =20mA		10		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.(T<sub>a</sub>=25°C)

[Unit: um]

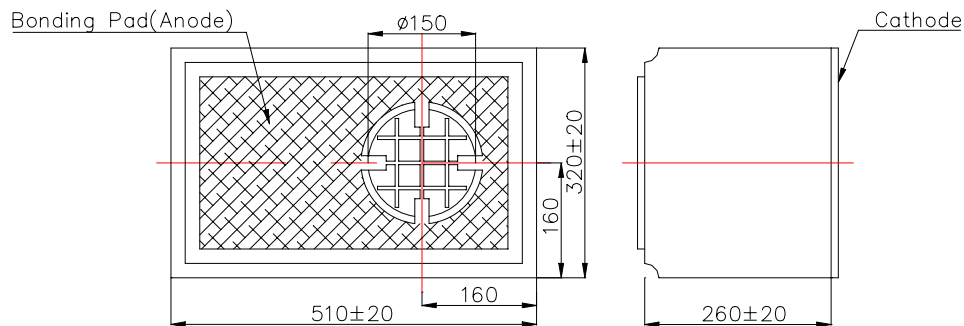


Fig.1 Electrode Pattern, Chip size and Emission Area